2-input NOR gate

Rev. 1 — 7 August 2012

Product data sheet

1. General description

74HC1G02-Q100 and 74HCT1G02-Q100 are high speed Si-gate CMOS devices. They provide a 2-input NOR function.

The standard output currents are half those of the 74HC02-Q100 and 74HCT02-Q100.

This product has been qualified to the Automotive Electronics Council (AEC) standard Q100 (Grade 1) and is suitable for use in automotive applications.

2. Features and benefits

- Automotive product qualification in accordance with AEC-Q100 (Grade 1)
 Specified from -40 °C to +85 °C and from -40 °C to +125 °C
- Input levels:
 - For 74HC1G02-Q100: CMOS level
 - For 74HCT1G02-Q100: TTL level
- Symmetrical output impedance
- High noise immunity
- Low power dissipation
- Balanced propagation delays
- ESD protection:
 - MIL-STD-883, method 3015 exceeds 2000 V
 - HBM JESD22-A114F exceeds 2000 V
 - MM JESD22-A115-A exceeds 200 V (C = 200 pF, R = 0 Ω)
- SOT353-1 and SOT753 package options

3. Ordering information

Table 1.Ordering information

Type number	Package							
	Temperature range	Name	Description	Version				
74HC1G02GW-Q100	–40 °C to +125 °C	TSSOP5	plastic thin shrink small outline package;	SOT353-1				
74HCT1G02GW-Q100			5 leads; body width 1.25 mm					
74HC1G02GV-Q100	–40 °C to +125 °C	SC-74A	plastic surface-mounted package; 5 leads	s SOT753				
74HCT1G02GV-Q100								

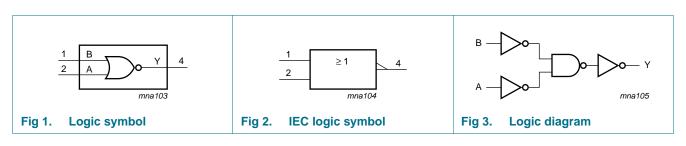


4. Marking

Table 2. Marking codes	
Type number	Marking ^[1]
74HC1G02GW-Q100	HB
74HCT1G02GW-Q100	ТВ
74HC1G02GV-Q100	H02
74HCT1G02GV-Q100	T02

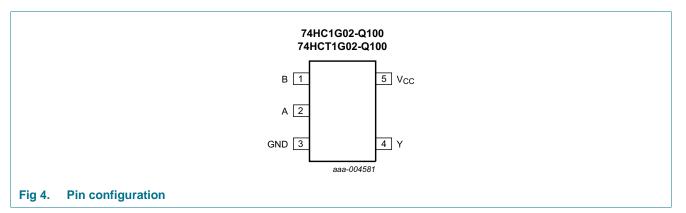
[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

5. Functional diagram



6. Pinning information

6.1 Pinning



6.2 Pin description

Table 3.	Pin description	
Symbol	Pin	Description
В	1	data input
А	2	data input
GND	3	ground (0 V)
Y	4	data output
V _{CC}	5	supply voltage

74HC HCT1G02 Q100

7. Functional description

Table 4. Function table

H = *HIGH* voltage level; *L* = *LOW* voltage level

Inputs		Output
Α	В	Y
L	L	Н
L	Н	L
Н	L	L
Н	Н	L

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V). [1]

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+7.0	V
I _{IK}	input clamping current	$V_{\rm I}$ < -0.5 V or $V_{\rm I}$ > $V_{\rm CC}$ + 0.5 V	-	±20	mA
Ι _{ΟΚ}	output clamping current	V_{O} < -0.5 V or V_{O} > V_{CC} + 0.5 V	-	±20	mA
I _O	output current	$-0.5 \text{ V} < \text{V}_{\text{O}} < \text{V}_{\text{CC}} + 0.5 \text{ V}$	-	±12.5	mA
I _{CC}	supply current		-	25	mA
I _{GND}	ground current		-25	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	$T_{amb} = -40 \ ^{\circ}C \text{ to } +125 \ ^{\circ}C$	[2] _	200	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] Above 55 °C, the value of P_{tot} derates linearly with 2.5 mW/K.

9. Recommended operating conditions

Table 6. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	74HC1	74HC1G02-Q100		74HCT1G02-Q100			Unit
			Min	Тур	Max	Min	Тур	Max	
V _{CC}	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V
VI	input voltage		0	-	V_{CC}	0	-	V _{CC}	V
Vo	output voltage		0	-	V _{CC}	0	-	V _{CC}	V
T _{amb}	ambient temperature		-40	+25	+125	-40	+25	+125	°C
$\Delta t / \Delta V$	input transition rise and fall rate	$V_{CC} = 2.0 V$	-	-	625	-	-	-	ns/V
		$V_{CC} = 4.5 V$	-	-	139	-	-	139	ns/V
		$V_{CC} = 6.0 V$	-	-	83	-	-	-	ns/V

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10. Static characteristics

Table 7. Static characteristics

Voltages are referenced to GND (ground = 0 V). All typical values are measured at T_{amb} = 25 °C.

Symbol	Parameter	Conditions	-40	–40 °C to +85 °C			–40 °C to +125 °C	
			Min	Тур	Max	Min	Max	
74HC1G0	2-Q100							
V _{IH}	HIGH-level input	$V_{CC} = 2.0 V$	1.5	1.2	-	1.5	-	V
	voltage	$V_{CC} = 4.5 V$	3.15	2.4	-	3.15	-	V
		$V_{CC} = 6.0 V$	4.2	3.2	-	4.2	-	V
	LOW-level input	V _{CC} = 2.0 V	-	0.8	0.5	-	0.5	V
	voltage	$V_{CC} = 4.5 V$	-	2.1	1.35	-	1.35	V
		$V_{CC} = 6.0 V$	-	2.8	1.8	-	1.8	V
V _{он}	HIGH-level output	$V_{I} = V_{IH}$ or V_{IL}						
	voltage	$I_{O} = -20 \ \mu A; \ V_{CC} = 2.0 \ V$	1.9	2.0	-	1.9	-	V
		$I_O = -20 \ \mu\text{A}; \ V_{CC} = 4.5 \ \text{V}$	4.4	4.5	-	4.4	-	V
		$I_{O} = -20 \ \mu A; \ V_{CC} = 6.0 \ V$	5.9	6.0	-	5.9	-	V
		I_{O} = -2.0 mA; V_{CC} = 4.5 V	4.13	4.32	-	3.7	-	V
		I_{O} = -2.6 mA; V_{CC} = 6.0 V	5.63	5.81	-	5.2	-	V
V _{OL} LOW-level output voltage	LOW-level output	$V_{I} = V_{IH} \text{ or } V_{IL}$						
	voltage	$I_0 = 20 \ \mu A; V_{CC} = 2.0 \ V$	-	0	0.1	-	0.1	V
		$I_0 = 20 \ \mu A; V_{CC} = 4.5 \ V$	-	0	0.1	-	0.1	V
		$I_0 = 20 \ \mu A; V_{CC} = 6.0 \ V$	-	0	0.1	-	0.1	V
		I_{O} = 2.0 mA; V_{CC} = 4.5 V	-	0.15	0.33	-	0.4	V
		$I_0 = 2.6 \text{ mA}; V_{CC} = 6.0 \text{ V}$	-	0.16	0.33	-	0.4	V
I	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 6.0$ V	-	-	1.0	-	1.0	μA
СС	supply current	$\label{eq:VI} \begin{array}{l} V_{I} = V_{CC} \text{ or } GND; \ I_{O} = 0 \ A; \\ V_{CC} = 6.0 \ V \end{array}$	-	-	10	-	20	μΑ
CI	input capacitance		-	- 1.5	-	-	-	pF
74HCT16	i02-Q100							
V _{IH}	HIGH-level input voltage	V_{CC} = 4.5 V to 5.5 V	2.0	1.6	-	2.0	-	V
V _{IL}	LOW-level input voltage	V_{CC} = 4.5 V to 5.5 V	-	1.2	0.8	-	0.8	V
V _{он}	HIGH-level output	$V_{I} = V_{IH}$ or V_{IL}						
	voltage	$I_{O} = -20 \ \mu A; V_{CC} = 4.5 \ V$	4.4	4.5	-	4.4	-	V
		I_{O} = -2.0 mA; V_{CC} = 4.5 V	4.13	4.32	-	3.7	-	V
/ _{OL}	LOW-level output	$V_{I} = V_{IH}$ or V_{IL}						
	voltage	$I_0 = 20 \ \mu A; \ V_{CC} = 4.5 \ V$	-	0	0.1	-	0.1	V
		$I_{O} = 2.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	0.15	0.33	-	0.4	V
I	input leakage current	$V_{I} = V_{CC}$ or GND; $V_{CC} = 5.5$ V	-	-	1.0	-	1.0	μA

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2-input NOR gate

Symbol	Parameter	Conditions	–40 °C to +85 °C			–40 °C	Unit	
			Min	Тур	Max	Min	Max	
I _{CC}	supply current		-	-	10	-	20	μA
ΔI_{CC}	additional supply current	per input; V _{CC} = 4.5 V to 5.5 V; V _I = V _{CC} - 2.1 V; I _O = 0 A	-	-	500	-	850	μA
CI	input capacitance			- 1.5	-	-	-	pF

Table 7. Static characteristics ...continued

11. Dynamic characteristics

Table 8. Dynamic characteristics

GND = 0 V; $t_r = t_f \le 6.0$ ns; All typical values are measured at $T_{amb} = 25$ °C. For test circuit see Figure 6

Symbol	Parameter	Conditions		–40 °C to +85 °C			–40 °C	Unit	
				Min	Тур	Max	Min	Max	
74HC1G	02-Q100					I	1	1	
t _{pd}	propagation delay	A and B to Y; see Figure 5	<u>[1]</u>						
		$V_{CC} = 2.0 \text{ V}; C_{L} = 50 \text{ pF}$		-	25	115	-	135	ns
		$V_{CC} = 4.5 \text{ V}; C_{L} = 50 \text{ pF}$		-	9	23	-	27	ns
		$V_{CC} = 5.0 \text{ V}; C_{L} = 15 \text{ pF}$		-	7	-	-	-	ns
		$V_{CC} = 6.0 \text{ V}; C_{L} = 50 \text{ pF}$		-	8	20	-	23	ns
C _{PD}	power dissipation capacitance	$V_I = GND$ to V_{CC}	[2]	-	18	-	-	-	pF
74HCT1	G02-Q100								
t _{pd}	propagation delay	A and B to Y; see Figure 5	<u>[1]</u>						
		$V_{CC} = 4.5 \text{ V}; C_{L} = 50 \text{ pF}$		-	11	24	-	27	ns
		$V_{CC} = 5.0 \text{ V}; \text{ C}_{L} = 15 \text{ pF}$		-	9	-	-	-	ns
C_{PD}	power dissipation capacitance	V_{I} = GND to V_{CC} – 1.5 V	[2]	-	19	-	-	-	pF

[1] t_{pd} is the same as t_{PLH} and t_{PHL} .

[2] $\ C_{PD}$ is used to determine the dynamic power dissipation P_D (\mu W).

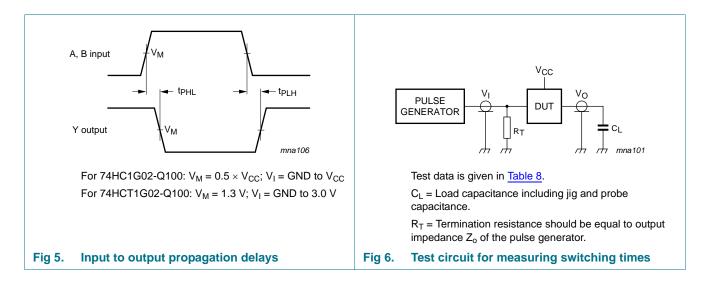
$$\begin{split} P_{D} &= C_{PD} \times V_{CC}^{2} \times f_{i} + \sum \left(C_{L} \times V_{CC}^{2} \times f_{o} \right) \text{ where:} \\ f_{i} &= \text{input frequency in MHz} \\ f_{o} &= \text{output frequency in MHz} \\ C_{L} &= \text{output load capacitance in pF} \end{split}$$

 V_{CC} = supply voltage in Volts

 $\Sigma (C_L \times V_{CC}^2 \times f_o) = \text{sum of outputs}$

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12. Waveforms



2-input NOR gate

13. Package outline

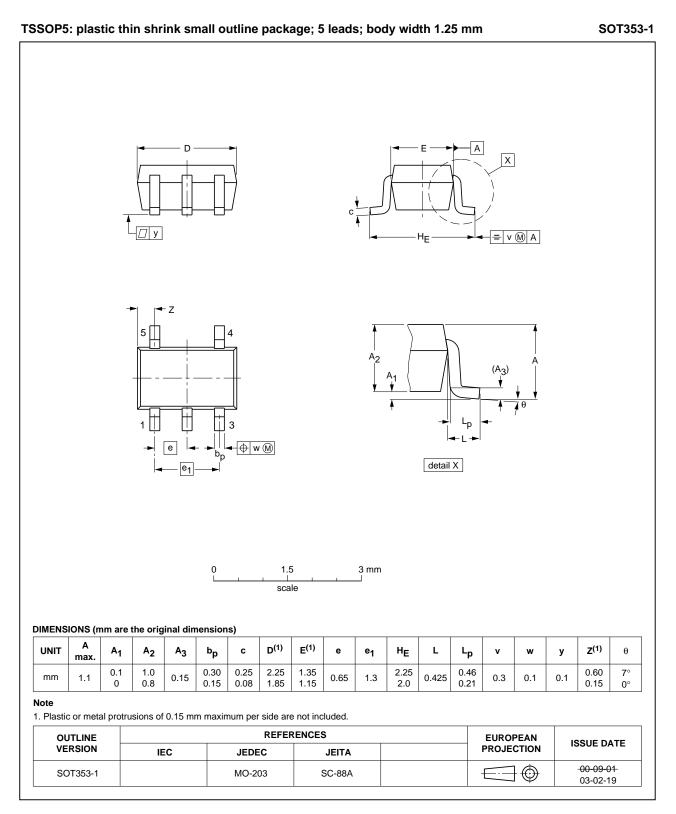


Fig 7. Package outline SOT353-1 (TSSOP5)

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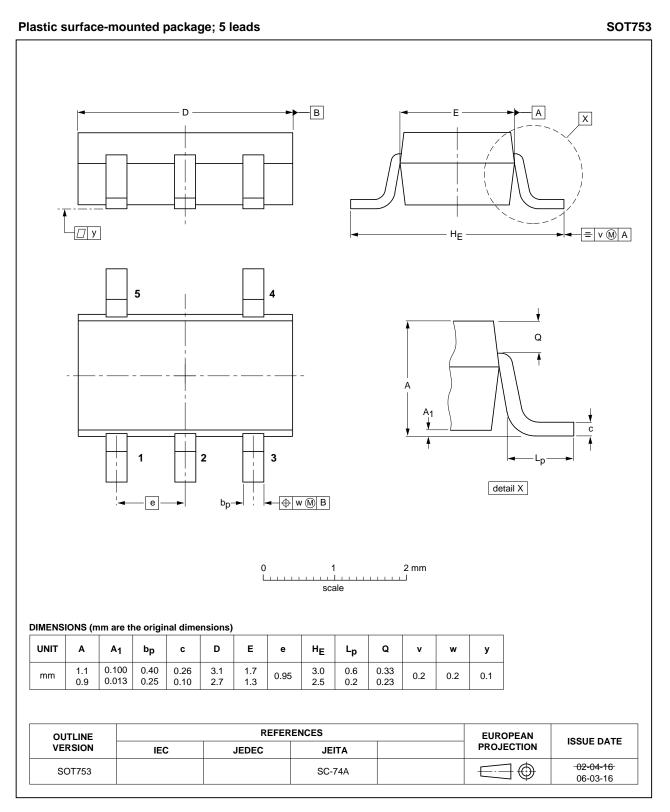


Fig 8. Package outline SOT753 (SC-74A)

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74HC_HCT1G02_Q100

14. Abbreviations

Table 9.	Abbreviations
Acronym	Description
CMOS	Complementary Metal Oxide Semiconductor
TTL	Transistor-Transistor Logic
HBM	Human Body Model
ESD	ElectroStatic Discharge
MM	Machine Model
DUT	Device Under Test
MIL	Military

15. Revision history

Table 10. Revision history				
Document ID	Release date	Data sheet status	Change notice	Supersedes
74HC_HCT1G02_Q100 v.1	20120807	Product data sheet	-	-

16. Legal information

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Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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